SILICON NPN TRIPLE DIFFUSED TYPE (PCT PROCESS)

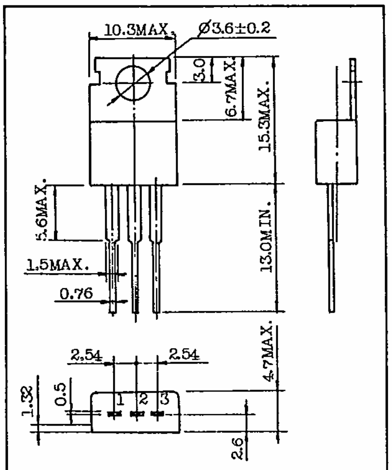
2SC1569

COLOR TV CHROMA OUTPUT APPLICATIONS.

FEATURES:

- High Voltage : V_{CEO}=300V
- Small Collector Output Capacitance : C_{ob}=5.0pF(Typ.)
- High Transition Frequency : f_T=100MHz (Typ.)

Unit in mm



1. BASE
2. COLLECTOR(HEAT SINK)
3. EMITTER

JEDED	TO — 220AB
EIAJ	SC — 46
TOSHIBA	2 — 10A1A

Mounting kit No. AC75
Weight : 1.9g

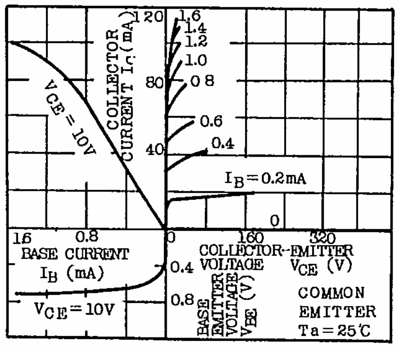
MAXIMUM RATINGS (Ta=25°C)

CHARACTERISTIC		SYMBOL	RATING	UNIT
Collector-Base Voltage		V_{CBO}	300	V
Collector-Emitter Voltage		V_{CEO}	300	V
Emitter-Base Voltage		V_{EBO}	5	V
Collector Current		I_C	150	mA
Emitter Current		I_E	-150	mA
Collector Power Dissipation	Ta=25°C	P_C	1.5	W
	Tc=25°C		12.5	
Junction Temperature		T_j	150	°C
Storage Temperature Range		T_{stg}	-55∿150	°C

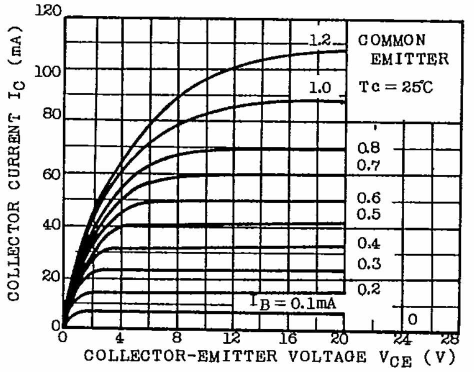
ELECTRICAL CHARACTERISTICS (Ta=25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=100V, I_E=0	-	-	1.0	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=5V, I_C=0	-	-	1.0	μA
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	I_C=5mA, I_B=0	300	-	-	V
DC Current Gain	h_{FE}	V_{CE}=10V, I_C=50mA	40	-	170	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=100mA, I_B=20mA	-	-	1.0	V
Base-Emitter Saturation Voltage	$V_{BE(sat)}$	I_C=100mA, I_B=20mA	-	-	1.2	V
Transition Frequency	f_T	V_{CE}=10V, I_C=30mA	40	100	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=50V, I_E=0, f=1MHz	-	5.0	6.5	pF

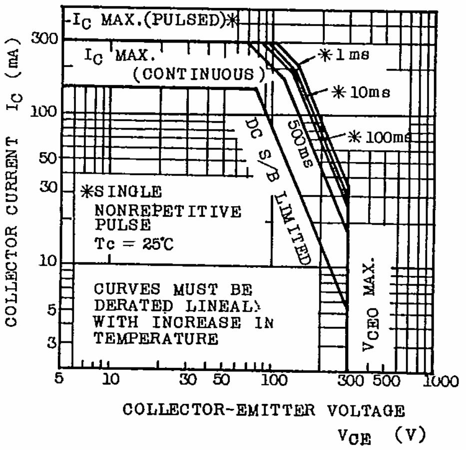
STATIC CHARACTERISTICS



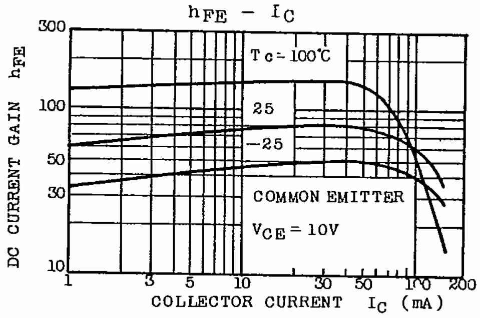
I_C – V_{CE} (LOW VOLTAGE REGION)



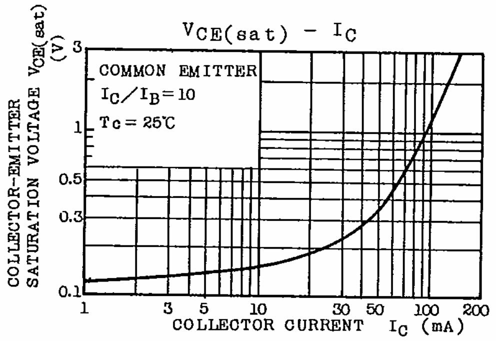
SAFE OPERATING AREA



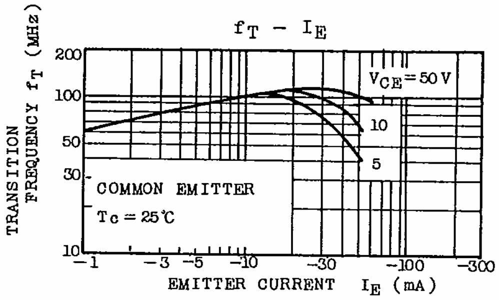
h_{FE} – I_C



$V_{CE(sat)}$ – I_C



f_T – I_E



C_{ob} – V_{CB}